

SDB(S)12 - SDB(S)115

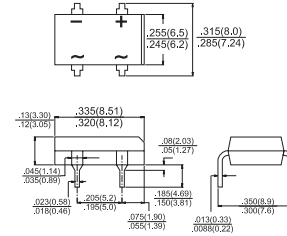
1.0 AMP. Schottky Barrier Bridge Rectifiers

DB

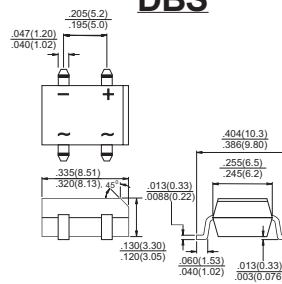


Features

- ✧ Metal to silicon rectifier, majority carrier conduction
- ✧ Low forward voltage drop
- ✧ Easy pick and place
- ✧ High surge current capability
- ✧ Plastic material used carriers Underwriters Laboratory Classification 94V-0
- ✧ Epitaxial construction
- ✧ High temperature soldering:
260°C/ 10 seconds at terminals
- ✧ Small size, single installation lead solderable per MIL-STD-202 Method 208



DBS



Mechanical Data

Dimensions in inches and (millimeters)

- ✧ Case: Molded plastic
- ✧ Terminals: Pure tin plated, lead free.
- ✧ Polarity: Indicated by cathode band

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	SDB 12	SDB 13	SDB 14	SDB 15	SDB 16	SDB 19	SDB 110	SDB 115	Units
		SDBS 12	SDBS 13	SDBS 14	SDBS 15	SDBS 16	SDBS 19	SDBS 110	SDBS 115	
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	20	30	40	50	60	90	100	150	V
Maximum RMS Voltage	V _{RMS}	14	21	28	35	42	63	70	105	V
Maximum DC Blocking Voltage	V _{DC}	20	30	40	50	60	90	100	150	V
Maximum Average Forward Rectified Current at T _L (See Fig. 1)	I _(AV)	1.0								A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	30								A
Maximum Instantaneous Forward Voltage (Note 1) @ 1.0A	V _F	0.5			0.75		0.80		0.95	V
Maximum DC Reverse Current @ T _A =25 °C at Rated DC Blocking Voltage @ T _A =100 °C	I _R	0.4					0.1			mA mA
		10			5.0		0.5			
Typical Junction Capacitance (Note 3)	C _j	50								pF
Typical Thermal Resistance (Note 2)	R _{θJL}	28								°C /W
	R _{θJA}	88								
Operating Temperature Range	T _J	-65 to +125			-65 to +150					°C
Storage Temperature Range	T _{STG}	-65 to +150								°C

- Notes:
1. Pulse Test with PW=300 usec, 1% Duty Cycle
 2. Measured on P.C.Board with 0.5" x 0.5" (12 mm x 12mm) Copper Pad Areas.
 3. Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.

RATINGS AND CHARACTERISTIC CURVES (SDB(S)12 THRU SDB(S)115)

FIG.1- MAXIMUM FORWARD CURRENT DERATING CURVE

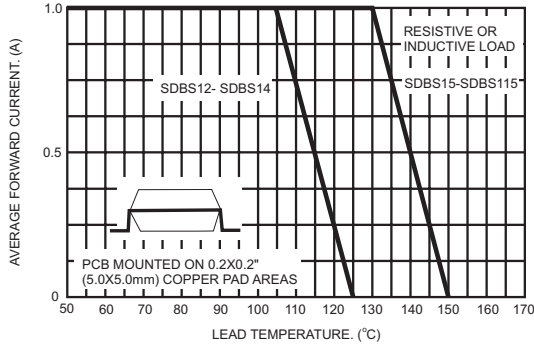


FIG.2- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

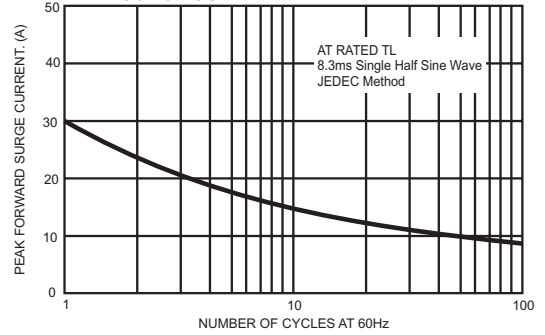


FIG.3- TYPICAL FORWARD CHARACTERISTICS

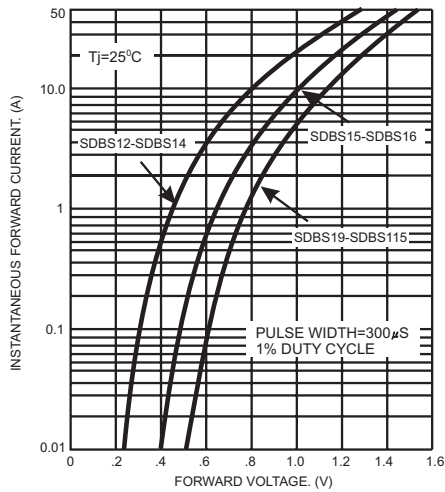


FIG.4- TYPICAL REVERSE CHARACTERISTICS

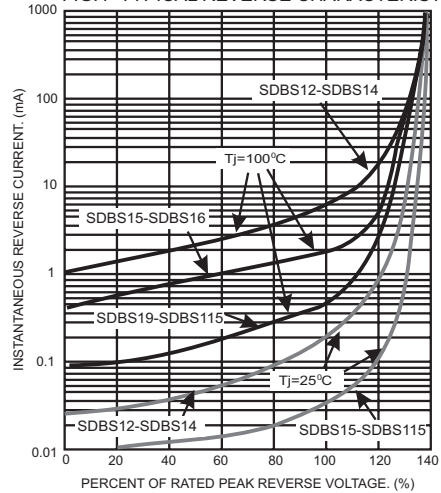


FIG.5- TYPICAL JUNCTION CAPACITANCE

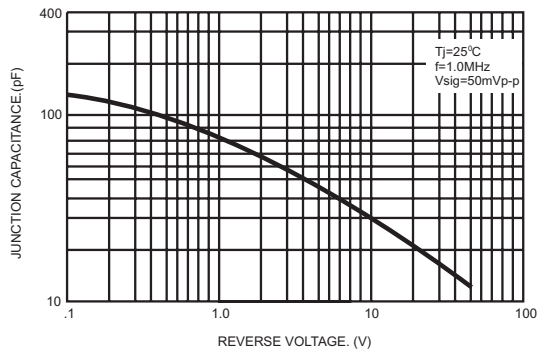


FIG.6- TYPICAL TRANSIENT THERMAL CHARACTERISTICS

